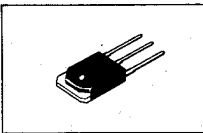




No.1267

2SD1400



NPN Triple Diffused Planar Type Silicon Transistor
FOR CTV HORIZONTAL DEFLECTION OUTPUT

Features:

- High breakdown voltage and high reliability
- High switching speed
- Capable of being mounted easily due to one-point fixing type plastic mold package

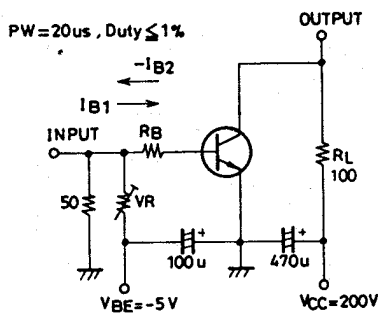
Absolute Maximum Ratings at Ta=25°C

| | | | unit |
|------------------------------|------|-------------|------|
| Collector to Base Voltage | VCBO | 1500 | V |
| Collector to Emitter Voltage | VCEO | 800 | V |
| Emitter to Base Voltage | VEBO | 7 | V |
| Collector Current | IC | 2.5 | A |
| Peak Collector Current | icp | 10 | A |
| Collector Dissipation | PC | 80 | W |
| Junction Temperature | Tj | 150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |

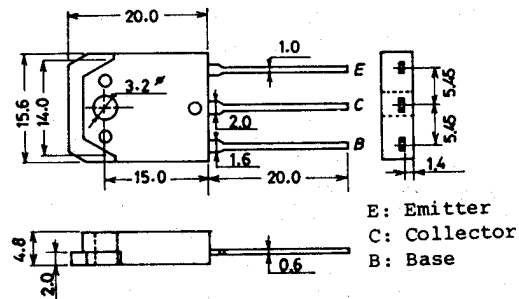
Electrical Characteristics at Ta=25°C

| | | | min | typ | max | unit |
|--------------------------|----------|-----------------------------|------|-----|-----|------|
| Collector Cutoff Current | ICBO | VCB=800V, IE=0 | | | 10 | uA |
| Emitter Cutoff Current | IEBO | VEB=5V, IC=0 | | | 1 | mA |
| DC Current Gain | hFE | VCE=5V, IC=0.5A | 8 | | | |
| Gain Bandwidth Product | fT | VCE=10V, IC=0.5A | | 3 | | MHz |
| C-E Saturation Voltage | VCE(sat) | IC=2A, IB=0.6A | | | 8 | V |
| B-E Saturation Voltage | VBE(sat) | IC=2A, IB=0.6A | | | 1.5 | V |
| C-B Breakdown Voltage | V(BR)CBO | IC=5mA, IE=0 | 1500 | | | V |
| C-E Breakdown Voltage | V(BR)CEO | IC=100mA, RBE=∞ | 800 | | | V |
| E-B Breakdown Voltage | V(BR)EBO | IE=200mA, IC=0 | 7 | | | V |
| Fall Time | tf | IC=2A, IB1=0, 6A, IB2=-1.2A | | | 0.7 | us |

Switching Time Test Circuit



Case Outline 2022 (unit:mm)



These specifications are subject to change without notice.